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ON Semiconductor®

Advanced Power MOSFET

IRFM120A

IEEE802.3af Compatible

FEATURES

- ❑ Avalanche Rugged Technology
- ❑ Rugged Gate Oxide Technology
- ❑ Lower Input Capacitance
- ❑ Improved Gate Charge
- ❑ Extended Safe Operating Area
- ❑ Lower Leakage Current : 10 μA (Max.) @ V_{DS} = 100V
- ❑ Lower $R_{DS(ON)}$: 0.155 Ω (Typ.)

BV_{DSS} = 100 V

$R_{DS(on)}$ = 0.2 Ω

I_D = 2.3 A

SOT-223

1. Gate 2. Drain 3. Source

Absolute Maximum Ratings

Symbol	Characteristic	Value	Units
V_{DSS}	Drain-to-Source Voltage	100	V
I_D	Continuous Drain Current (T_A=25℃)	2.3	A
	Continuous Drain Current (T_A=70℃)	1.84	
I_{DM}	Drain Current-Pulsed ①	18	A
V_{GS}	Gate-to-Source Voltage	±20	V
E_{AS}	Single Pulsed Avalanche Energy ②	123	mJ
I_{AR}	Avalanche Current ①	2.3	A
E_{AR}	Repetitive Avalanche Energy ①	0.24	mJ
dv/dt	Peak Diode Recovery dv/dt ③	6.5	V/ns
P_D	Total Power Dissipation (T_A=25℃) *	2.4	W
	Linear Derating Factor *	0.019	W/℃
T_J , T_{STG}	Operating Junction and Storage Temperature Range	- 55 to +150	℃
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5-seconds	300	

Thermal Resistance

Symbol	Characteristic	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient *	--	52	℃/W

* When mounted on the minimum pad size recommended (PCB Mount).

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IRFM120A/D

Electrical Characteristics (T_A=25℃ unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
BV_{DSS}	Drain-Source Breakdown Voltage	100	--	--	V	V_{GS}=0V,I_D=250μA
$\Delta BV/\Delta T_J$	Breakdown Voltage Temp. Coeff.	--	0.12	--	V/℃	I_D=250μA ***See Fig 7***
$V_{GS(th)}$	Gate Threshold Voltage	2.0	--	4.0	V	V_{DS}=5V,I_D=250μA
I_{GSS}	Gate-Source Leakage , Forward	--	--	100	nA	V_{GS}=20V
	Gate-Source Leakage , Reverse	--	--	-100		V_{GS}=-20V
I_{DSS}	Drain-to-Source Leakage Current	--	--	1	μA	V_{DS}=30V ⑥
		--	--	10		V_{DS}=100V
		--	--	100		V_{DS}=80V,T_A=125℃
$R_{DS(on)}$	Static Drain-Source On-State Resistance	--	--	0.2	Ω	V_{GS}=10V,I_D=1.15A ④
g_{fs}	Forward Transconductance	--	3.12	--	S	V_{DS}=40V,I_D=1.15A ④
C_{iss}	Input Capacitance	--	370	480	pF	V_{GS}=0V,V_{DS}=25V,f =1MHz ***See Fig 5***
C_{oss}	Output Capacitance	--	95	110		
C_{rss}	Reverse Transfer Capacitance	--	38	45		
$t_{d(on)}$	Turn-On Delay Time	--	14	40	ns	V_{DD}=50V,I_D=9.2A, R_G=18Ω ***See Fig 13*** ④ ⑤
t_r	Rise Time	--	14	40		
$t_{d(off)}$	Turn-Off Delay Time	--	36	90		
t_f	Fall Time	--	28	70		
Q_g	Total Gate Charge	--	16	22	nC	V_{DS}=80V,V_{GS}=10V, I_D=9.2A ***See Fig 6 & Fig 12*** ④ ⑤
Q_{gs}	Gate-Source Charge	--	2.7	--		
Q_{gd}	Gate-Drain("Miller") Charge	--	7.8	--		

Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
I_S	Continuous Source Current	--	--	2.3	A	Integral reverse pn-diode in the MOSFET
I_{SM}	Pulsed-Source Current ①	--	--	18		
V_{SD}	Diode Forward Voltage ④	--	--	1.5	V	T_J=25℃,I_S=2.3A,V_{GS}=0V
t_{rr}	Reverse Recovery Time	--	98	--	ns	T_J=25℃,I_F=9.2A
Q_{rr}	Reverse Recovery Charge	--	0.34	--	μC	di_F/dt=100A/μs ④

Notes ;

① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature

② L=35mH, I_{AS}=2.3A, V_{DD}=25V, R_G=27Ω, Starting T_J=25℃

③ I_{SD}≤9.2A, di/dt≤300A/μs, V_{DD}≤BV_{DSS} , Starting T_J=25℃

④ Pulse Test : Pulse Width = 250μs, Duty Cycle ≤ 2%

⑤ Essentially Independent of Operating Temperature

⑥ Adjusted for Cisco

Fig 1. Output Characteristics

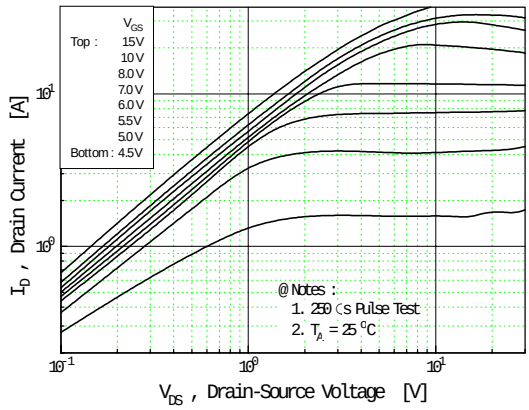


Fig 2. Transfer Characteristics

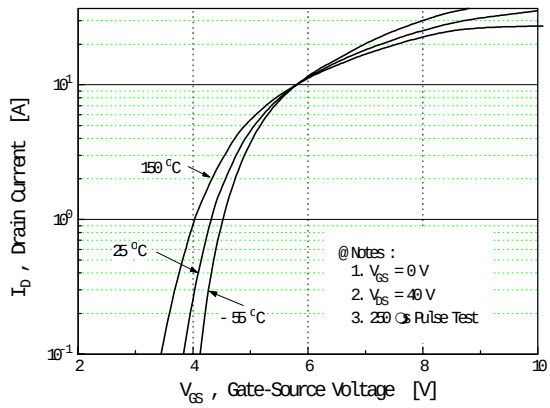


Fig 3. On-Resistance vs. Drain Current

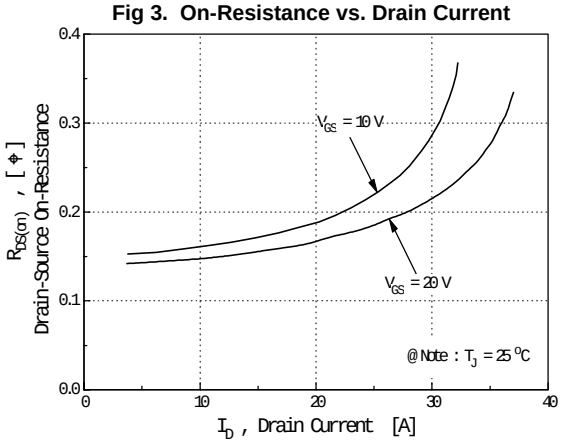


Fig 4. Source-Drain Diode Forward Voltage

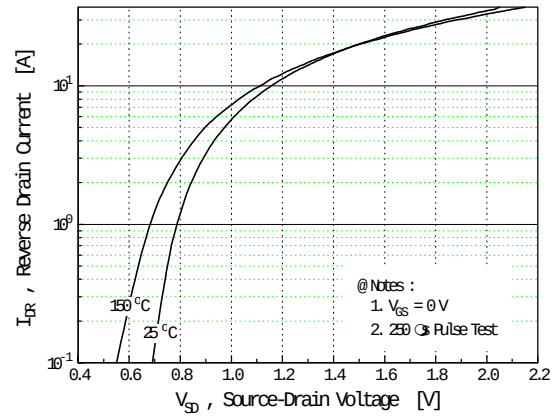


Fig 5. Capacitance vs. Drain-Source Voltage

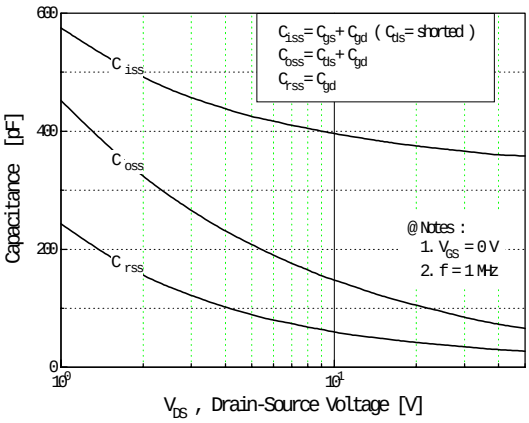


Fig 6. Gate Charge vs. Gate-Source Voltage

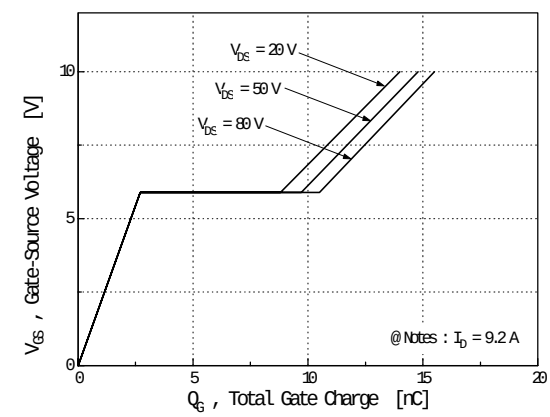


Fig 7. Breakdown Voltage vs. Temperature

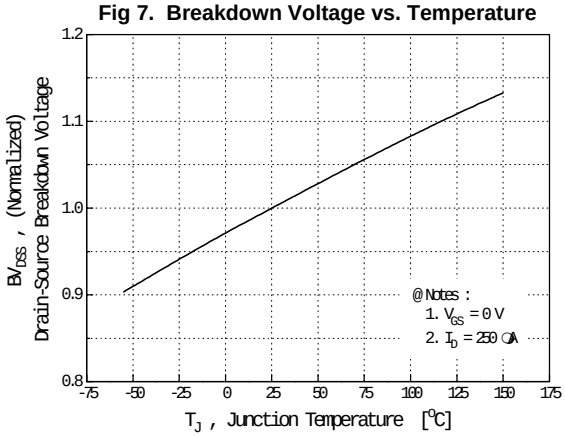


Fig 8. On-Resistance vs. Temperature

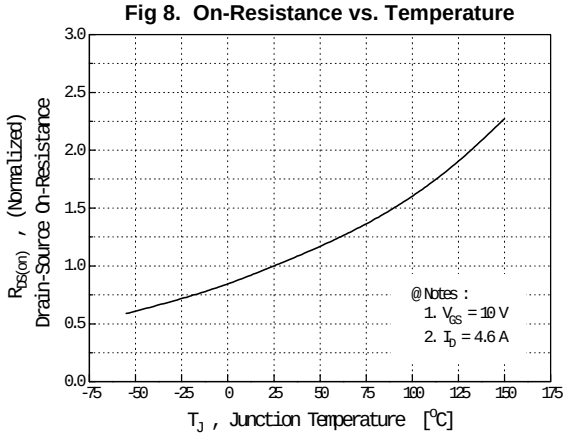


Fig 9. Max. Safe Operating Area

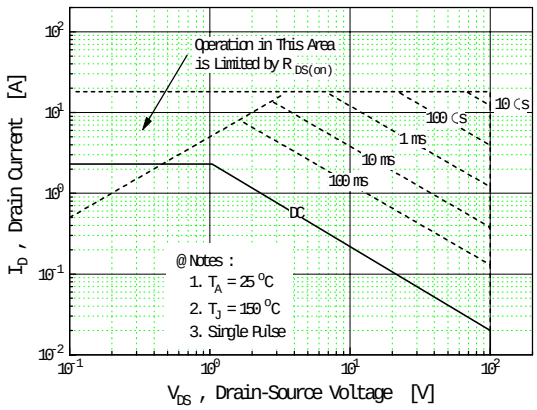


Fig 10. Max. Drain Current vs. Ambient Temperature

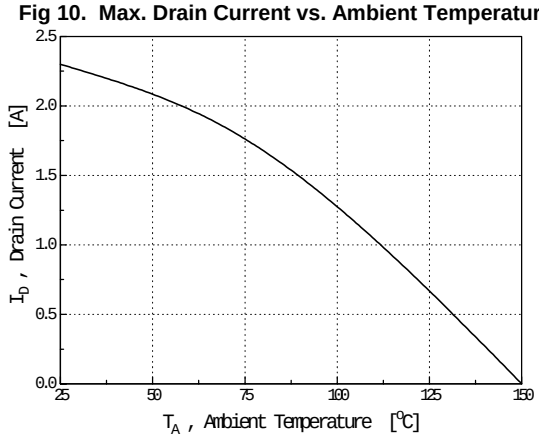


Fig 11. Thermal Response

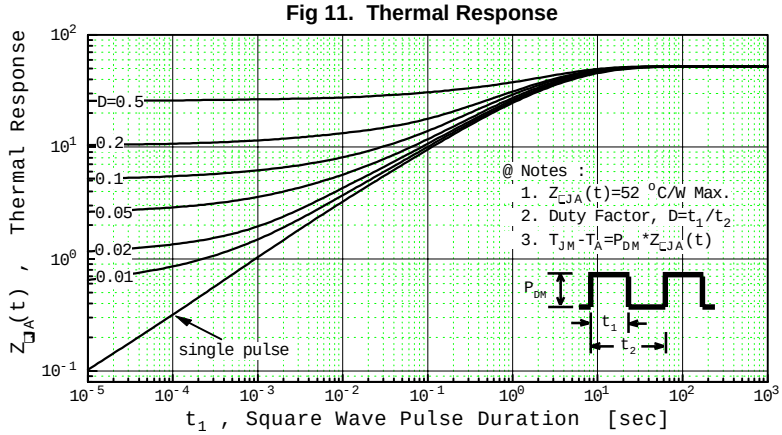


Fig 12. Gate Charge Test Circuit & Waveform

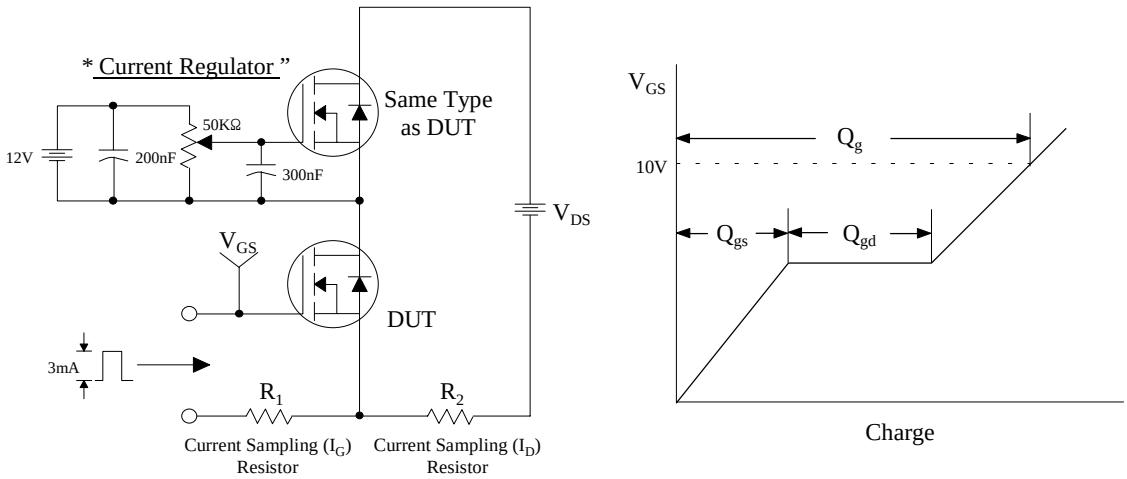


Fig 13. Resistive Switching Test Circuit & Waveforms

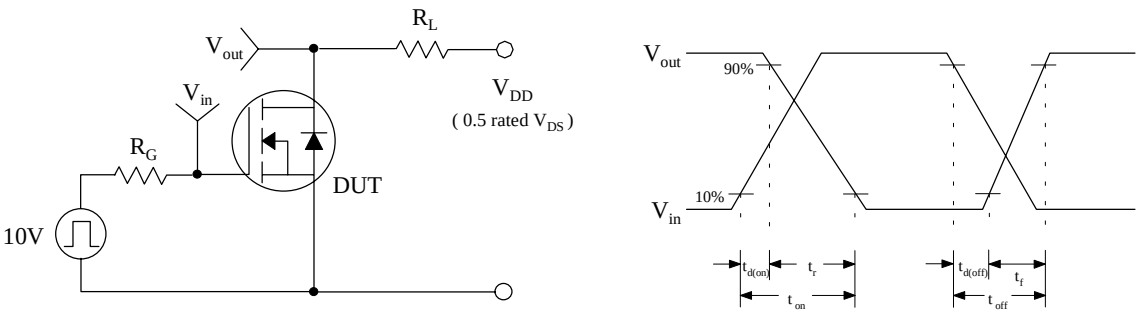


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

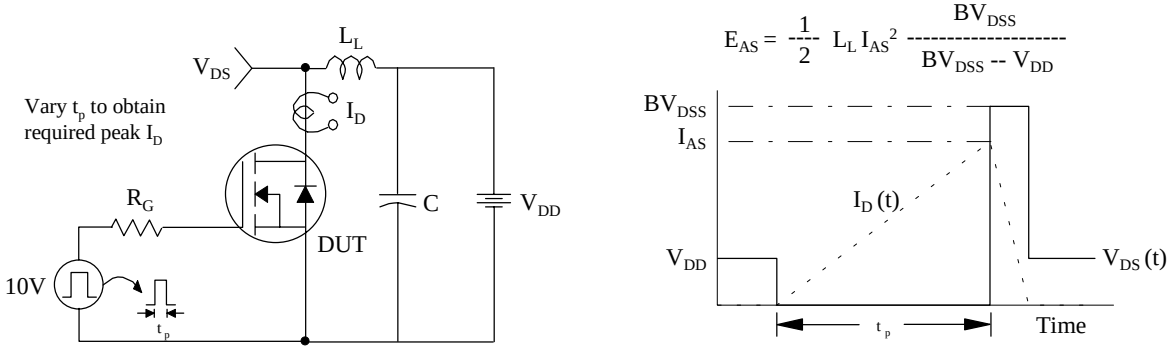
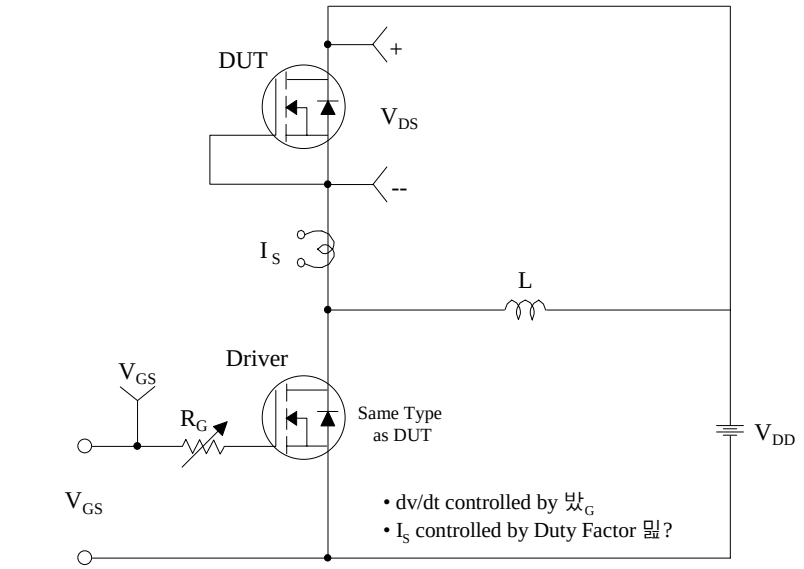
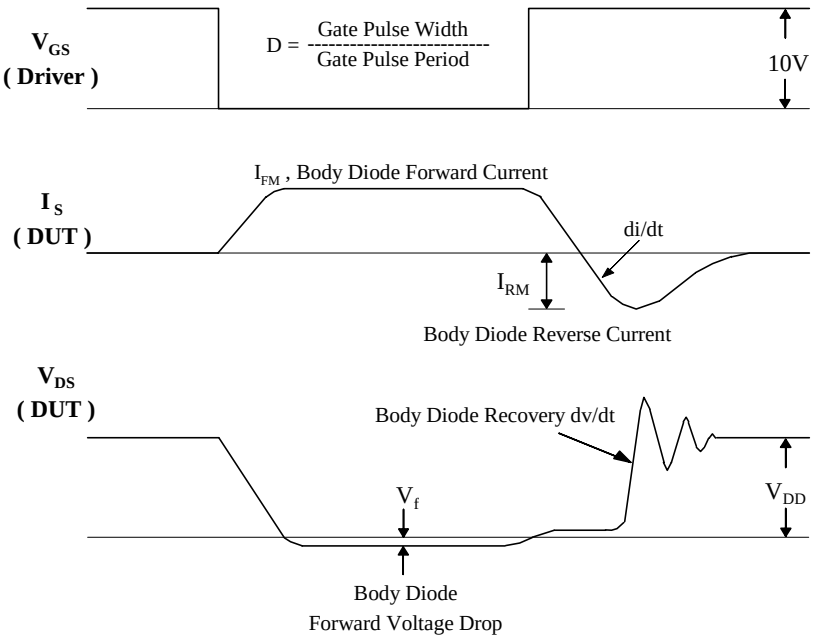


Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms





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